

Divya Somvanshi

List of Publications by Year in descending order

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34

papers

511

citations

759233

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all docs

34

docs citations

34

times ranked

625

citing authors

#	ARTICLE	IF	CITATIONS
1	First-principal insight of the gold-metal interaction to bilayer MoSe ₂ of AB and AA stacking order. Solid State Communications, 2022, 342, 114613.	1.9	3
2	Strain-dependent doping behavior of WSe ₂ monolayer: A first-principle calculation. Europhysics Letters, 2022, 137, 26004.	2.0	4
3	Theoretical Insights into Gold Metal Contacts to Monolayer and Bilayer MoSe ₂ . , 2021, , .		0
4	Improved Current Density and Contact Resistance in Bilayer MoSe ₂ Field Effect Transistors by AlO _x Capping. ACS Applied Materials & Interfaces, 2020, 12, 36355-36361.	8.0	31
5	Transition metal dichalcogenides based two-dimensional heterostructures for optoelectronic applications. , 2020, , 125-149.		15
6	A systematic study on the electronic structure of 3d, 4d, and 5d transition metal-doped WSe ₂ monolayer. Superlattices and Microstructures, 2020, 148, 106746.	3.1	12
7	Optical and Electrical Characterization of n-MoS ₂ /p-Si Heterojunction Diode. , 2020, , .		0
8	Recent Progress on Extended Wavelength and Split-Off Band Heterostructure Infrared Detectors. Micromachines, 2020, 11, 547.	2.9	6
9	Functionalized polyvinyl chloride/layered double hydroxide nanocomposites and its thermal and mechanical properties. Journal of Applied Polymer Science, 2020, 137, 48894.	2.6	8
10	Reduced Dark Current With a Specific Detectivity Advantage in Extended Threshold Wavelength Infrared Detector. , 2019, 3, 1-4.		3
11	Accuracy of activation energy from Arrhenius plots and temperature-dependent internal photoemission spectroscopy. Infrared Physics and Technology, 2019, 102, 103026.	2.9	4
12	Analysis of Extended Threshold Wavelength Photoresponse in Nonsymmetrical p-GaAs/AlGaAs Heterostructure Photodetectors. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-7.	2.9	5
13	Analysis of Barrier Parameters on the Extended Threshold Wavelength of Infrared Detectors. IEEE Photonics Technology Letters, 2018, 30, 1617-1620.	2.5	3
14	Effective Richardson Constant of Sol-Gel Derived TiO ₂ Films in n-TiO ₂ /p-Si Heterojunctions. IEEE Electron Device Letters, 2017, 38, 633-636.	3.9	30
15	Nature of carrier injection in metal/2D-semiconductor interface and its implications for the limits of contact resistance. Physical Review B, 2017, 96, .	3.2	55
16	Electrical and Ultraviolet-A Detection Properties of E-Beam Evaporated n-TiO ₂ Capped p-Si Nanowires Heterojunction Photodiodes. IEEE Nanotechnology Magazine, 2016, , 1-1.	2.0	20
17	Ultraviolet Detection Properties of p-Si/n-TiO ₂ Heterojunction Photodiodes Grown by Electron-Beam Evaporation and Sol-gel Methods: A Comparative Study. IEEE Nanotechnology Magazine, 2016, 15, 193-200.	2.0	64
18	Structural and optical characteristics of n-TiO ₂ thin films by sol-gel method. , 2015, , .		2

#	ARTICLE	IF	CITATIONS
19	Sol-Gel-Based Highly Sensitive Pd/n-ZnO Thin Film/n-Si Schottky Ultraviolet Photodiodes. IEEE Transactions on Electron Devices, 2015, 62, 1879-1884.	3.0	55
20	Electrical and Ultraviolet Detection Properties of n -ZnO Thin Film/p-Si Heterojunction Diodes Using a ZnO Buffer Layer. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 219-225.	0.5	1
21	Electrical and optical characterization of Pd/ZnO nanorods (NRs) Schottky diodes grown on n-Si substrates., 2014, .,		2
22	Effects of Sn and Zn Seed Layers on the Electrical Characteristics of Pd/ZnO Thin-Film Schottky Diodes Grown on n-Si Substrates. IEEE Electron Device Letters, 2014, 35, 945-947.	3.9	7
23	Pd/ZnO Nanoparticles Based Schottky Ultraviolet Photodiodes Grown on Sn-Coated n-Si Substrates by Thermal Evaporation Method. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 120-125.	2.9	24
24	Analysis of Temperature-Dependent Electrical Characteristics of n-ZnO Nanowires (NWs)/p-Si Heterojunction Diodes. IEEE Nanotechnology Magazine, 2014, 13, 62-69.	2.0	44
25	Electrical characteristics of Pd/ZnO nanowires (NWs)-based Schottky diodes grown on Zn seed layercoated n-Si substrates., 2014, .,		0
26	Effect of ZnO Seed Layer on the Electrical Characteristics of Pd/ZnO Thin-Film-Based Schottky Contacts Grown on n-Si Substrates. IEEE Nanotechnology Magazine, 2014, 13, 1138-1144.	2.0	11
27	Electrical Characterization of n-ZnO Nanowires/p-Si Based Heterojunction Diodes. Environmental Science and Engineering, 2014, , 589-592.	0.2	1
28	Analysis of $I = A(V - \phi)$ Characteristics of Pd/ZnO Thin Film/n-Si Schottky Diodes with Series Resistance. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 21-26.	0.5	23
29	Catalyst free growth of ZnO nanorods by thermal evaporation method., 2013, .,		3
30	Mean Barrier Height and Richardson Constant for Pd/ZnO Thin Film-Based Schottky Diodes Grown on n-Si Substrates by Thermal Evaporation Method. IEEE Electron Device Letters, 2013, 34, 1238-1240.	3.9	52
31	Synthesis and optical properties of zinc oxide nanoparticles grown on Sn-coated silicon substrate by thermal evaporation method., 2013, .,		1
32	Ultraviolet Detection Characteristics of Pd/n-ZnO Thin Film Schottky Photodiodes Grown on n-Si Substrates. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 349-354.	0.5	15
33	Boosting Principal Component Analysis by Genetic Algorithm. Defence Science Journal, 2010, 60, 392-398.	0.8	5
34	Fabrication and Characterization of ZnO Nanowires by Thermal Oxidation Method. Advanced Materials Research, 0, 585, 124-128.	0.3	2